

2N2906A, L JAN, JTX, JTXV, JANS
2N2906AUA JAN, JTX, JTXV, JANS
2N2906AUB JAN, JTX, JTXV, JANS
2N2907A, L JAN, JTX, JTXV, JANS
2N2907AUA JAN, JTX, JTXV, JANS
2N2907AUB JAN, JTX, JTXV, JANS



Processed per MIL-PRF-19500/291

PNP SILICON SMALL-SIGNAL TRANSISTORS

MAXIMUM RATINGS

Ratings	Symbol	All Types		Units
Collector-Emitter Voltage	V_{CE0}	60		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current	I_C	600		mAdc
		A, L, AUB⁽¹⁾	AUA⁽²⁾	
Total Power Dissipation @ $T_A = 25^{\circ}C$	P_T	0.5	0.65	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$

1) Derate linearly 3.08 mW/ $^{\circ}C$ above $T_A = +37.5^{\circ}C$.

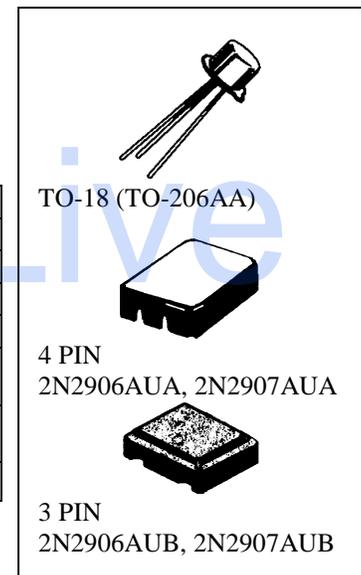
2) Derate linearly 4.76 mW/ $^{\circ}C$ above $T_A = +63.5^{\circ}C$.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10$ mAdc	$V_{(BR)CEO}$	60		Vdc
Collector-Base Cutoff Current $V_{CE} = 60$ Vdc	I_{CBO1}		10	μ Adc
Collector-Base Cutoff Current $V_{CE} = 50$ Vdc	I_{CBO}		10	η Adc
Collector-Base Cutoff Current $V_{CE} = 50$ Vdc	I_{CES}		50	η Adc
Emitter-Base Cutoff Current $V_{EB} = 5.0$ Vdc	I_{EBO1}		10	μ Adc
Emitter-Base Cutoff Current $V_{EB} = 4.0$ Vdc	I_{EBO}		50	η Adc



S2N2906A, L, AUA, AUB; S2N2907A, L, AUA, AUB JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS				
Forward-Current Transfer Ratio I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc} UA,UB	S2N2906A., L, UA, UB S2N2907A, L,	40 75	175	
I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} UB	S2N2906A, L, UA, UB S2N2907A, L, UA,	40 100	450	
I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} UB	S2N2906A., L, UA, UB S2N2907A, L, UA,	40 100	120 300	
I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc} UB	S2N2906A, L, UA, UB S2N2907A, L, UA,	40 50		
I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc} UB	S2N2906A, L, UA, UB S2N2907A, L, UA,			
Collector-Emitter Saturation Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{CE(sat)}		0.4 1.6	V _{dc}
Base-Emitter Saturation Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{BE(sat)}	0.6	1.3 2.6	V _{dc}
DYNAMIC CHARACTERISTICS				
Forward Current Transfer Ratio V _{CE} = 10 V _{dc} , I _C = 1.0 mA _{dc} , f = 1.0 kHz UA,UB	S2N2906A, L, UA,UB S2N2907A, L,	h _{fe}	40 100	
Magnitude of Small-Signal Forward Current Transfer Ratio V _{CE} = 20 V _{dc} , I _C = 20 mA _{dc} , f = 100 MHz	h _{fe}	2.0		
Output Capacitance V _{CB} = 10 V _{dc} , I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{obo}		8.0	pF
Input Capacitance V _{EB} = 2.0 V _{dc} , I _C = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{ibo}		30	pF